



HIGH SPEED NPN POWER TRANSISTORS

**GE13070P
GE13071P**

**400 & 450 VOLTS
5 AMPS, 100 WATTS**

The GE13070P and GE13071P transistors are designed for high-voltage, high-speed power switching in inductive circuits where fall time is critical. They are particularly suited for line-operated switch-mode applications such as:

Features:

- Switching regulators
- Inverters
- Solenoid and relay drivers
- Motor controls
- Deflection circuits

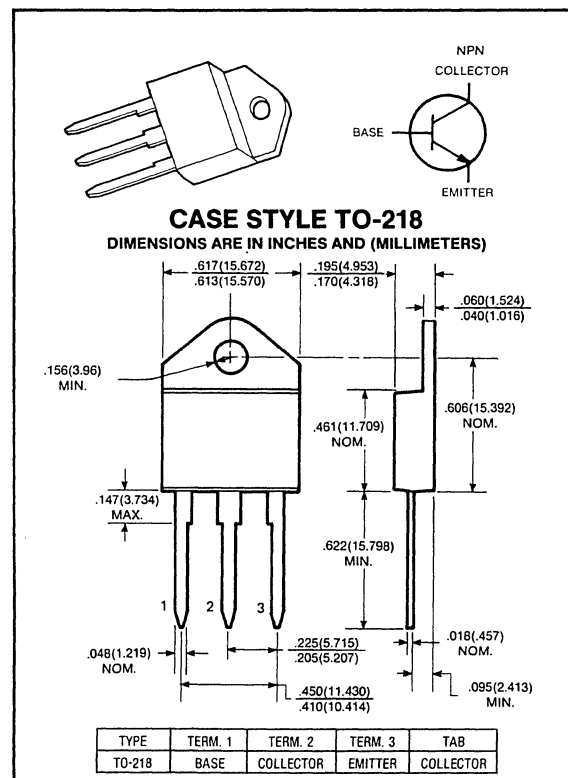
Fast Turn-Off Times:

- 100 ns inductive fall time @ 25°C (Typ)
- 150 ns inductive crossover time @ 25°C (Typ)
- 400 ns inductive storage time @ 25°C (Typ)

Operating temperature range -65 to +150°C

100°C Performance Specified for:

- Switching times with inductive loads —
- Saturation voltages
- Leakage currents



maximum ratings ($T_A = 25^\circ\text{C}$) (unless otherwise specified)

RATING	SYMBOL	GE13070P	GE13071P	UNITS
Collector-Emitter Voltage	V_{CEO}	400	450	Volts
Collector-Emitter Voltage	V_{CEV}	650	750	Volts
Emitter Base Voltage	V_{EBO}	6	6	Volts
Collector Current — Continuous	I_C	5	5	A
Peak (Repetitive) ⁽¹⁾	I_{CM}	8	8	A
Base Current — Continuous	I_B	2	2	A
Peak (Non-Repetitive) ⁽¹⁾	I_{BM}	4	4	A
Total Power Dissipation @ $T_c = 25^\circ\text{C}$	P_D	100	100	Watts
@ $T_c = 100^\circ\text{C}$		40	40	
Derate above 25°C		0.8	0.8	W/°C
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-65 to +150	-65 to +150	°C

thermal characteristics

Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.25	1.25	°C/W
Maximum Lead Temperature for Soldering Purpose: 1/8" from Case for 5 Seconds	T_L	275	275	°C

(1) Pulse Test: Pulse Width = 5ms. Duty Cycle ≤ 10%.

electrical characteristics ($T_C = 25^\circ\text{C}$) (unless otherwise specified)

CHARACTERISTIC	SYMBOL	MIN	TYP	MAX	UNIT
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off characteristics⁽¹⁾

Collector-Emitter Sustaining Voltage ($I_C = 100\text{mA}$, $I_B = 0$)	GE13070P GE13071P	$V_{CEO(sus)}$	400 450	— —	— —	Volts
Collector Cutoff Current ($V_{CEV} = \text{Rated Value}$, $V_{BE(off)} = 1.5\text{V}$) ($V_{CEV} = \text{Rated Value}$, $V_{BE(off)} = 1.5\text{V}$, $T_C = 100^\circ\text{C}$)		I_{CEV}	— —	— —	0.5 2.5	mA
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEV}$, $R_{BE} = 50\Omega$, $T_C = 100^\circ\text{C}$)		I_{CER}	—	—	3.0	mA
Emitter Cutoff Current ($V_{EB} = 6\text{V}$, $I_C = 0$)		I_{EBO}	—	—	1.0	mA

on characteristics⁽¹⁾

DC Current Gain ($I_C = 3\text{A}$, $V_{CE} = 5\text{V}$)		h_{FE}	8	—	—	—
Collector-Emitter Saturation Voltage ($I_C = 3\text{A}$, $I_B = .6\text{A}$) ($I_C = 5\text{A}$, $I_B = 1\text{A}$) ($I_C = 3\text{A}$, $I_B = .6\text{A}$, $T_C = 100^\circ\text{C}$)		$V_{CE(sat)}$	— — —	— — —	1 3 2	V
Base-Emitter Saturation Voltage ($I_C = 3\text{A}$, $I_B = .6\text{A}$) ($I_C = 3\text{A}$, $I_B = .6\text{A}$, $T_C = 100^\circ\text{C}$)		$V_{BE(sat)}$	— —	— —	1.5 1.5	V

switching characteristics

Resistive Load							
Delay Time	(V _{CC} = 250V, I _C = 3A I _{B1} = .4A, t _p = 30 μs Duty Cycle < 2%, V _{BE(OFF)} = 5V)		t _d	—	.03	.05	μs
Rise Time			t _r	—	.10	.4	
Storage Time			t _s	—	.4	1.5	
Fall Time			t _f	—	.175	.5	
Inductive Load, Clamped							
Storage Time	I _{C(pk)} = 3A I _{B1} = .4A V _{BE(off)} = 5V V _{CE(PK)} = 250V	(T _J = 100°C)	t _{sv}	—	.7	2	μs
Crossover Time			t _c	—	.28	.5	
Fall Time			t _{fi}	—	.15	.3	
Storage Time		(T _J = 25°C)	t _{sv}	—	.4	—	
Crossover Time			t _c	—	.15	—	
Fall Time			t _{fi}	—	.1	—	

(1) Pulse Test: Pulse Width - $300\mu\text{s}$ Duty Cycle $\leq 2\%$.